

MITSUBISHI SEMICONDUCTOR &lt;GaAs FET&gt;

**MGF1952A**

Microwave Power MES FET (Leadless Ceramic Package)

**DESCRIPTION**

The MGF1952A is designed for use in S to Ku band power amplifiers.

The lead-less ceramic package assures minimum parasitic losses.

**FEATURES**

High gain and High P1dB

Glp=7.0dB , P1dB=17dBm (Typ.) @ f=12GHz

**APPLICATION**

S to Ku band power Amplifiers

**QUALITY GRADE**

GG

**ORDERING INFORMATION**

Tape & reel 3000pcs./reel

**Outline Drawing**

Fig.1

**ABSOLUTE MAXIMUM RATINGS** (Ta=25°C)

Symbol	Parameter	Ratings	Unit
V <sub>GDO</sub>	Gate to drain voltage	-8	V
V <sub>GSO</sub>	Gate to source voltage	-8	V
I <sub>D</sub>	Drain current	240	mA
PT	Total power dissipation	600	mW
T <sub>ch</sub>	Channel temperature	125	°C
T <sub>stg</sub>	Storage temperature	-65 to +125	°C

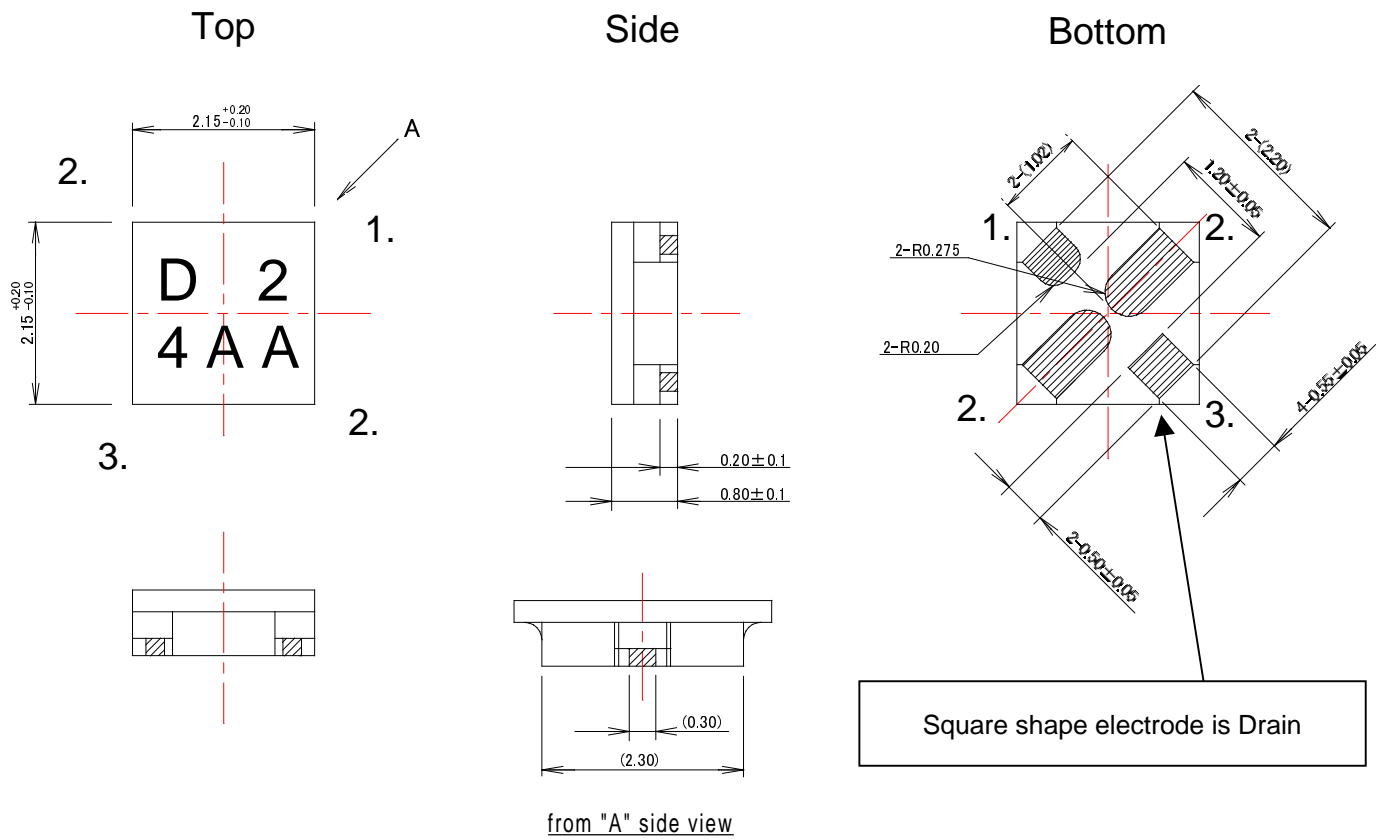
**Keep Safety first in your circuit designs!**  
Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measure such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

**ELECTRICAL CHARACTERISTICS** (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			MIN.	TYP.	MAX	
V(BR)GDO	Gate to drain breakdown voltage	I <sub>g</sub> =-60μA	-8	-15	--	V
I <sub>DSS</sub>	Saturated drain current	V <sub>GS</sub> =0V, V <sub>DS</sub> =3V	65	120	240	mA
V <sub>GS(off)</sub>	Gate to source cut-off voltage	V <sub>DS</sub> =3V, I <sub>D</sub> =600μA	-0.3	-1.4	-3.5	V
P1dB	Output Power at 1dB gain Compression	V <sub>DS</sub> =3V, I <sub>D</sub> =60mA f=12GHz	15	17	--	dBm
Glp	Linear Power Gain	V <sub>DS</sub> =3V, I <sub>D</sub> =60mA f=12GHz, Pin=-5dBm	5	7	--	dB

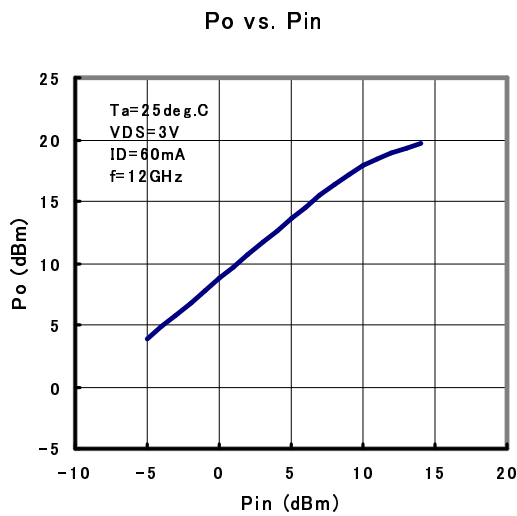
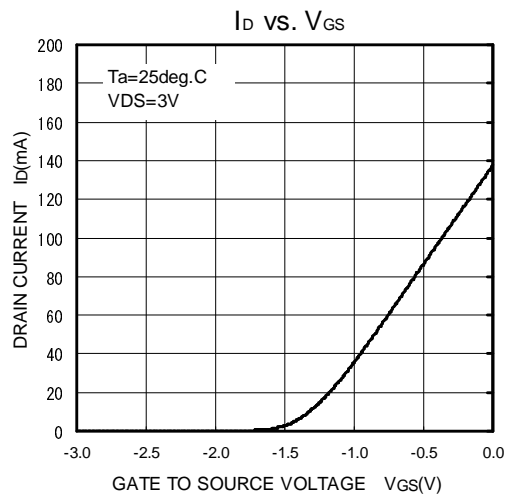
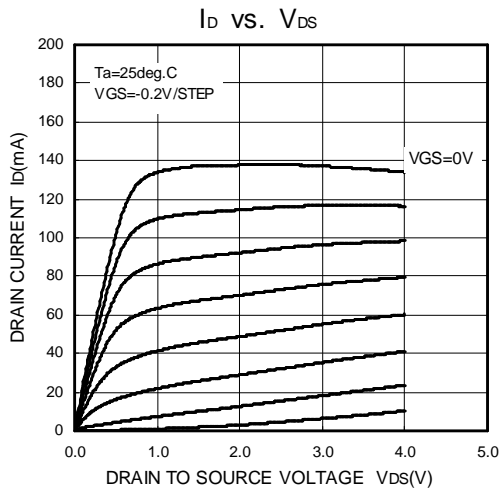
Fig.1

Unit : mm



- 1. Gate
- 2. Source
- 3. Drain

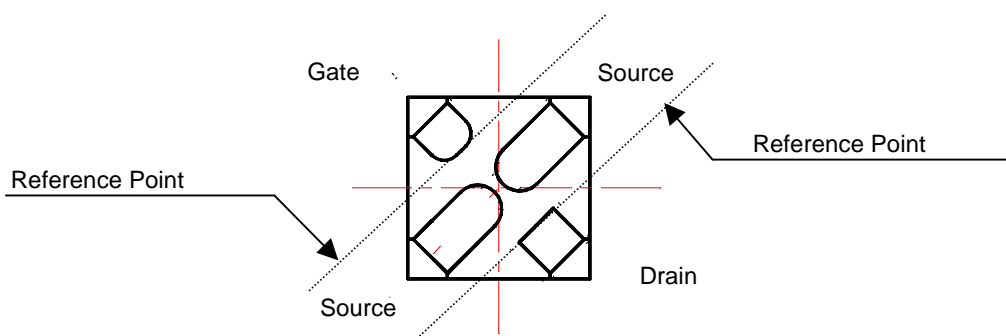
TYPICAL CHARACTERISTICS (Ta=25°C)



S PARAMETERS

(Conditions : VDS=3V, ID=60mA, Ta=25deg.C)

f (GHz)	S11		S21		S12		S22		K	MAG/MSG (dB)
	Mag.	Angle	Mag.	Angle	Mag.	Angle	Mag.	Angle		
1	0.963	-32.6	6.695	154.5	0.024	72.0	0.314	-24.7	0.21	24.4
2	0.888	-66.5	6.024	128.4	0.043	52.3	0.297	-51.3	0.38	21.4
3	0.822	-89.7	5.294	110.6	0.056	42.0	0.281	-66.0	0.51	19.7
4	0.764	-114.3	4.599	93.5	0.065	32.3	0.259	-83.0	0.64	18.5
5	0.720	-132.8	4.030	79.6	0.071	24.2	0.254	-94.1	0.77	17.5
6	0.685	-149.2	3.591	67.1	0.075	19.2	0.250	-100.0	0.90	16.8
7	0.660	-165.2	3.243	54.4	0.079	14.0	0.247	-104.2	1.01	15.5
8	0.643	-179.8	2.993	42.2	0.082	9.4	0.243	-108.3	1.10	13.7
9	0.629	165.3	2.785	30.5	0.088	4.4	0.232	-111.5	1.15	12.6
10	0.624	150.0	2.614	18.5	0.095	-0.8	0.214	-115.4	1.17	11.9
11	0.618	133.3	2.460	6.4	0.099	-8.3	0.179	-119.8	1.25	11.0
12	0.620	115.8	2.310	-6.9	0.104	-14.8	0.137	-125.6	1.29	10.2
13	0.639	98.6	2.163	-19.8	0.107	-21.6	0.085	-134.3	13.27	9.6
14	0.670	81.9	2.017	-33.9	0.111	-30.5	0.025	-176.9	1.32	9.2
15	0.709	66.3	1.846	-47.2	0.113	-39.4	0.063	61.7	1.33	8.7
16	0.765	52.1	1.700	-60.1	0.113	-48.6	0.145	47.0	1.25	8.8
17	0.815	37.9	1.537	-73.9	0.112	-57.5	0.237	37.8	1.18	8.8
18	0.850	25.1	1.353	-88.1	0.109	-67.0	0.328	29.2	1.16	8.5



### Requests Regarding Safety Designs

Mitsubishi Electric constantly strives to raise the level of its quality and reliability. Despite these concerted efforts, however, there will be occasions when our semiconductor products suffer breakdowns, malfunctions or other problems. In view of this reality, it is requested that every feasible precaution be taken in the pursuit of redundancy design, malfunction prevention design and other safety-related designs, to prevent breakdowns or malfunctions in our products from resulting in accidents involving people, fires, social losses or other problems, thereby upholding the highest levels of safety in the products when in use by customers.

### Matters of Importance when Using these Materials

1. These materials are designed as reference materials to ensure that all customers purchase Mitsubishi Electric semiconductors best suited to their specific use applications. Please be aware, however, that the technical information contained in these materials does not comprise consent for the execution or use of intellectual property rights or other rights owned by Mitsubishi Electric Corporation.
2. Mitsubishi Electric does not assume responsibility for damages resulting from the use of product data, graphs, charts, programs, algorithms or other applied circuit examples described in these materials, or for the infringement of the rights of third-party owners resulting from such use.
3. The data, graphs, charts, programs, algorithms and all other information described in these materials were current at the issue of these materials, with Mitsubishi Electric reserving the right to make any necessary updates or changes in the products or specifications in these materials without prior notice. Before purchasing Mitsubishi Electric semiconductor products, therefore, please obtain the latest available information from Mitsubishi Electric directly or an authorized dealer.
4. Every possible effort has been made to ensure that the information described in these materials is fully accurate. However, Mitsubishi Electric assumes no responsibility for damages resulting from inaccuracies occurring within these materials.
5. When using the product data, technical contents indicated on the graphs, charts, programs or algorithms described in these materials, assessments should not be limited to only the technical contents, programs and algorithm units. Rather, it is requested that ample evaluations be made of each individual system as a whole, with the customer assuming full responsibility for decisions on the propriety of application. Mitsubishi Electric does not accept responsibility for the propriety of application.
6. The products described in these materials, with the exception of special mention concerning use and reliability, have been designed and manufactured with the purpose of use in general electronic machinery. Accordingly these products have not been designed and manufactured with the purpose of application in machinery or systems that will be used under conditions that can affect human life, or in machinery or systems used in social infrastructure that demand a particularly high degree of reliability. When considering the use of the products described in these materials in transportation machinery (automobiles, trains, vessels), for objectives related to medical treatment, aerospace, nuclear power control, submarine repeaters or systems or other specialized applications, please consult with Mitsubishi Electric directly or an authorized dealer.
7. When considering use of products for purposes other than the specific applications described in these materials, please inquire at Mitsubishi Electric or an authorized dealer.
8. The prior consent of Mitsubishi Electric in writing is required for any reprinting or reproduction of these materials.
9. Please direct any inquiries regarding further details of these materials, or any other comments or matters of attention, to Mitsubishi Electric or an authorized dealer.